

# TrenchP™ Power MOSFETs

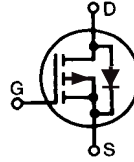
## IXTA28P065T IXTP28P065T

$$V_{DSS} = -65V$$

$$I_{D25} = -28A$$

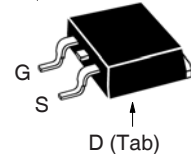
$$R_{DS(on)} \leq 45m\Omega$$

P-Channel Enhancement Mode  
Avalanche Rated

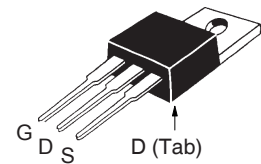


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	- 65	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	- 65	V
$V_{GSS}$	Continuous	$\pm 15$	V
$V_{GSM}$	Transient	$\pm 25$	V
$I_{D25}$	$T_C = 25^\circ C$	- 28	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	- 90	A
$I_A$	$T_C = 25^\circ C$	- 28	A
$E_S$	$T_C = 25^\circ C$	200	mJ
$P_D$	$T_C = 25^\circ C$	83	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3.0	g
	TO-263	2.5	g

TO-263 AA (IXTA)



TO-220AB (IXTP)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low  $R_{DS(ON)}$  and  $Q_G$

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	- 65		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	- 2.5		- 4.5 V
$I_{GSS}$	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$			$\pm 50$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			- 3 $\mu A$ -100 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			45 m $\Omega$

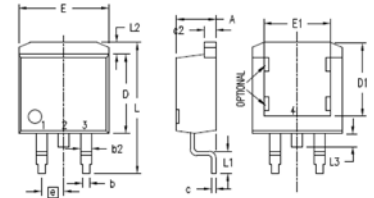
Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1	10	16	S
C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -25V, f = 1MHz		2030	pF
C <sub>oss</sub>			270	pF
C <sub>rss</sub>			127	pF
t <sub>d(on)</sub>	<b>Resistive Switching Times</b> V <sub>GS</sub> = -10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub> R <sub>G</sub> = 10Ω (External)		21	ns
t <sub>r</sub>			29	ns
t <sub>d(off)</sub>			36	ns
t <sub>f</sub>			23	ns
Q <sub>g(on)</sub>			V <sub>GS</sub> = -10V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 • I <sub>D25</sub>	
Q <sub>gs</sub>	20	nC		
Q <sub>gd</sub>	10	nC		
R <sub>thJC</sub>	TO-220		0.50	1.5 °C/W
R <sub>thCS</sub>				°C/W

### Source-Drain Diode

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I <sub>s</sub>	V <sub>GS</sub> = 0V			-28 A
I <sub>SM</sub>	Repetitive, Pulse Width Limited by T <sub>JM</sub>			-112 A
V <sub>SD</sub>	I <sub>F</sub> = -28A, V <sub>GS</sub> = 0V, Note 1			-1.5 V
t <sub>rr</sub>	I <sub>F</sub> = -14A, -di/dt = -100A/μs V <sub>R</sub> = -33V, V <sub>GS</sub> = 0V		31	ns
Q <sub>RM</sub>			34	nC
I <sub>RM</sub>			-2.2	A

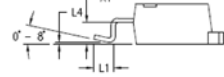
Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

### TO-263 Outline



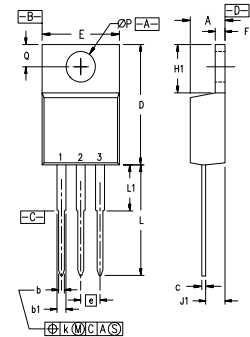
Pins:

- 1 - Gate
- 2,4 - Drain
- 3 - Source



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

### TO-220 Outline



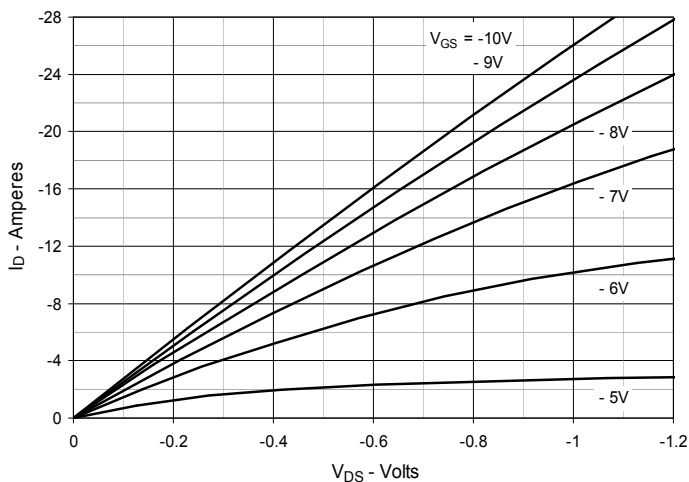
- Pins: 1 - Gate 2 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

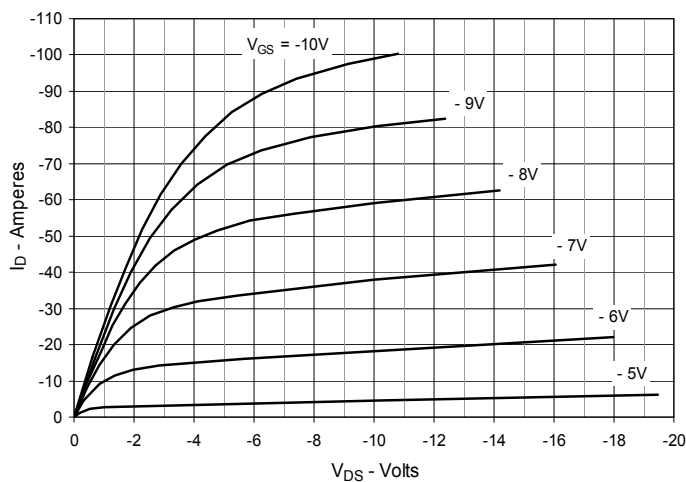
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

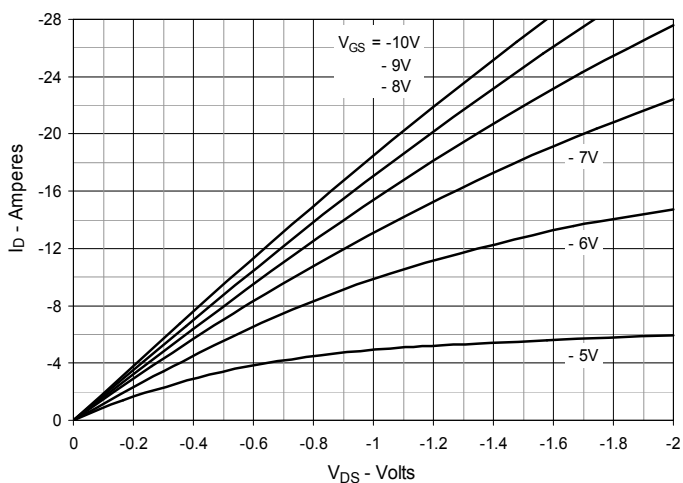
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



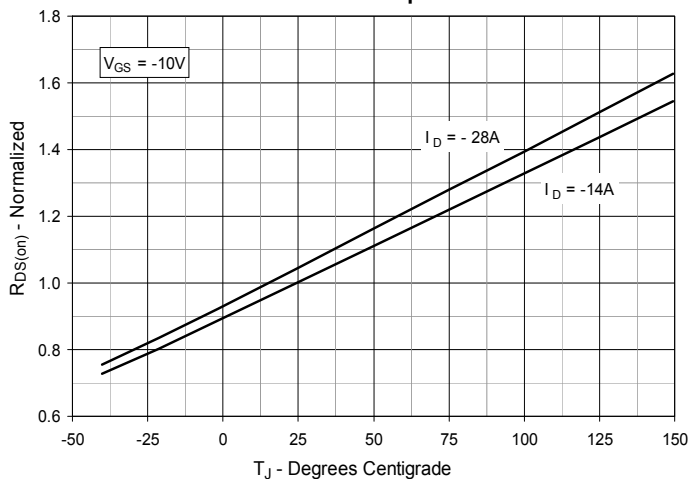
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



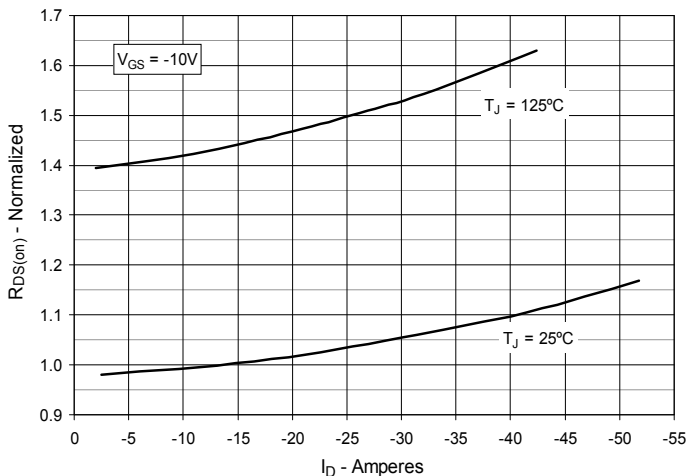
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -14\text{A}$  Value vs. Junction Temperature**



**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -14\text{A}$  Value vs. Drain Current**



**Fig. 6. Maximum Drain Current vs. Case Temperature**

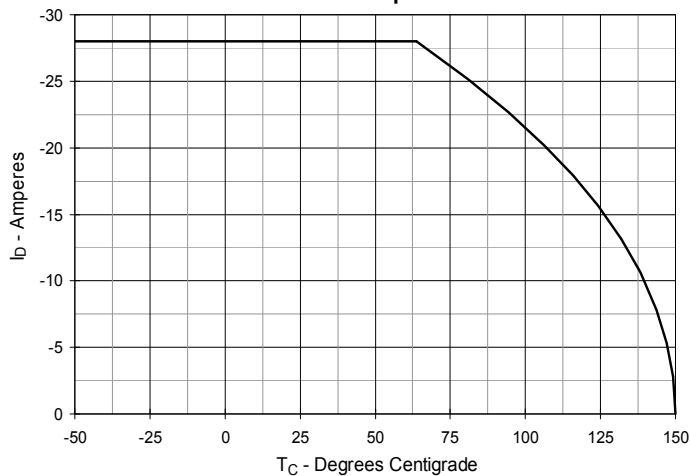


Fig. 7. Input Admittance

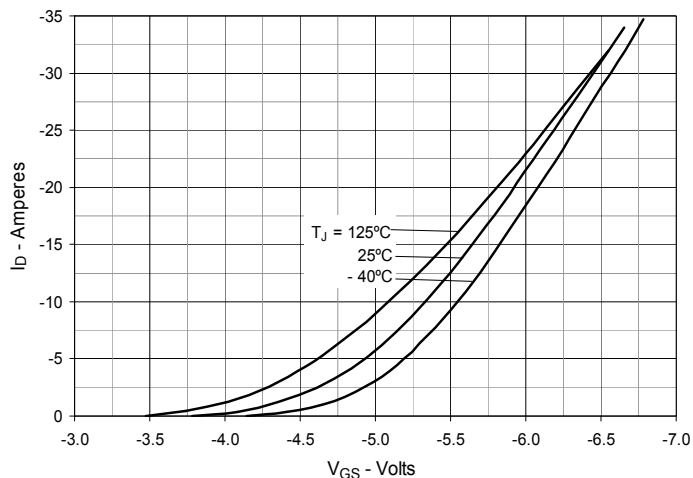


Fig. 8. Transconductance

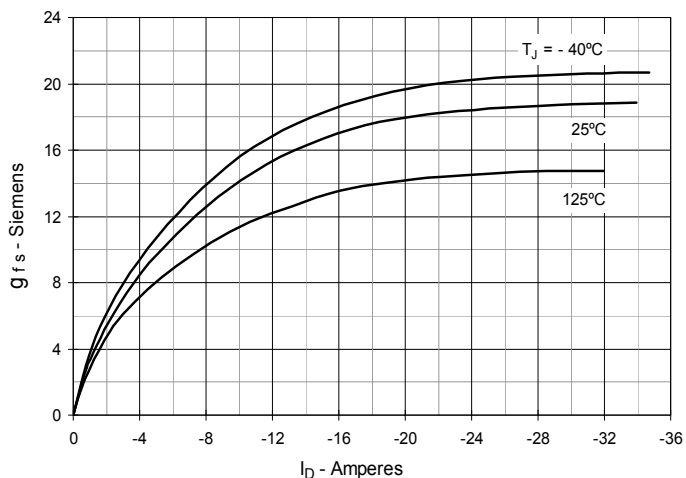


Fig. 9. Forward Voltage Drop of Intrinsic Diode

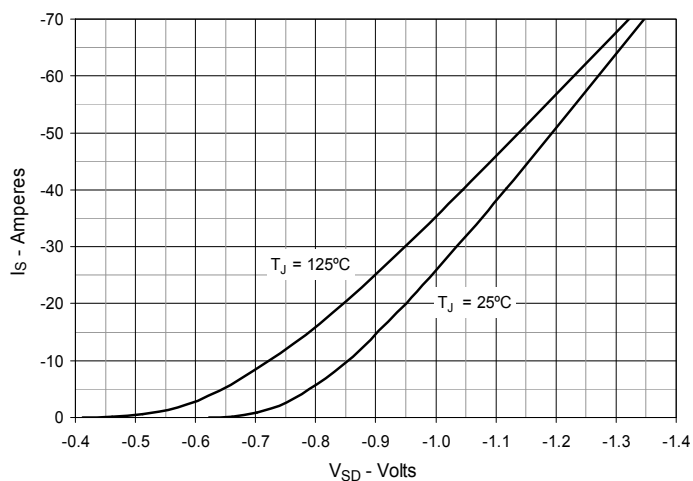


Fig. 10. Gate Charge

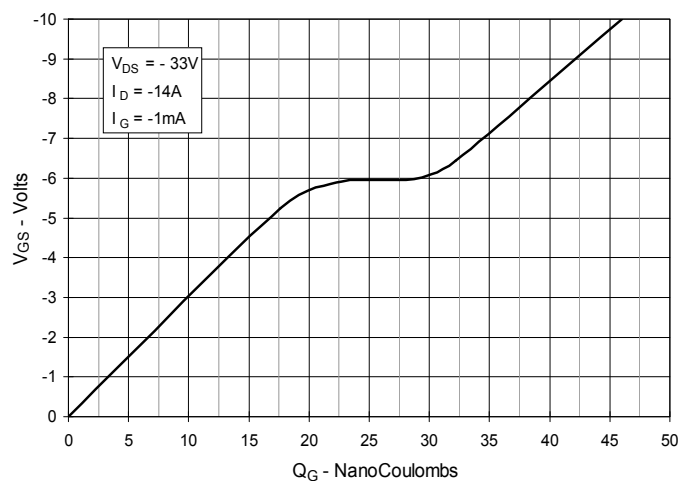


Fig. 11. Capacitance

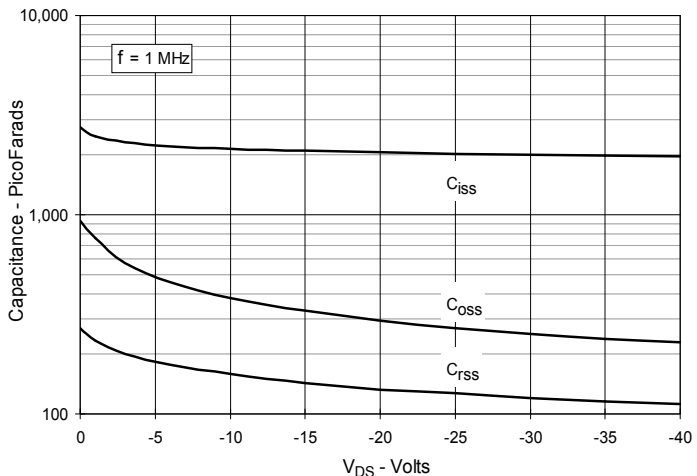
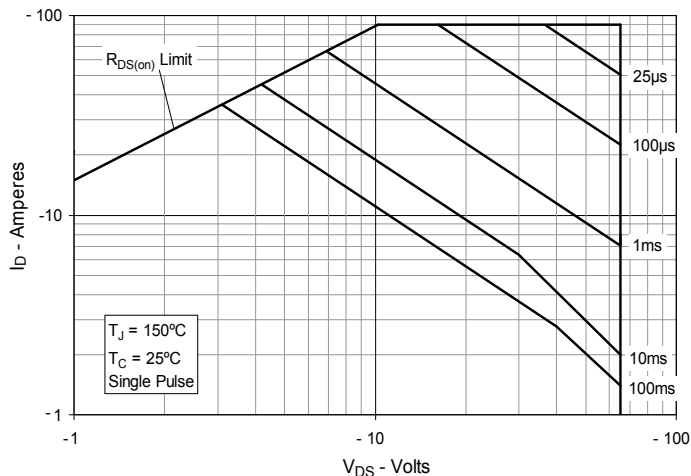
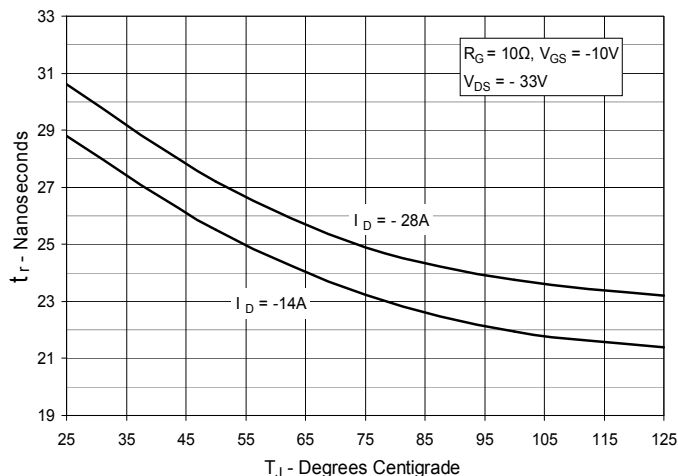


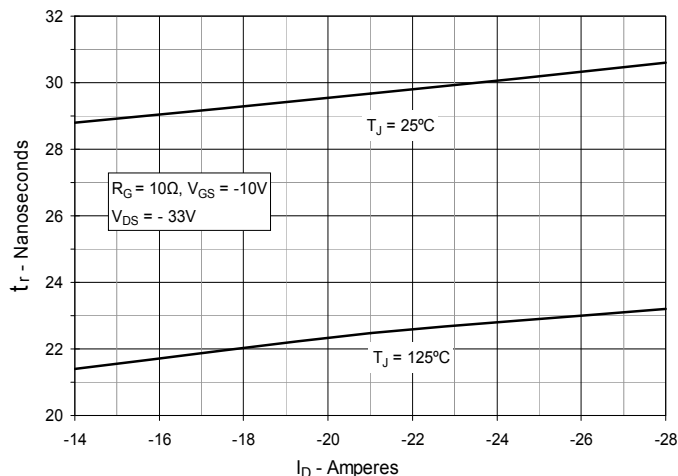
Fig. 12. Forward-Bias Safe Operating Area



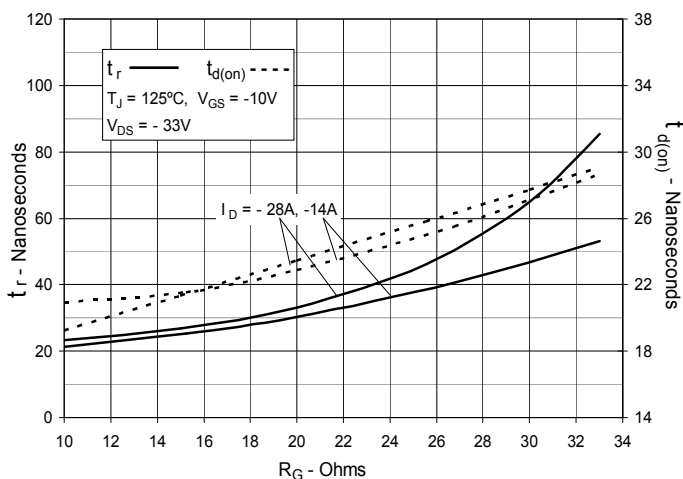
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



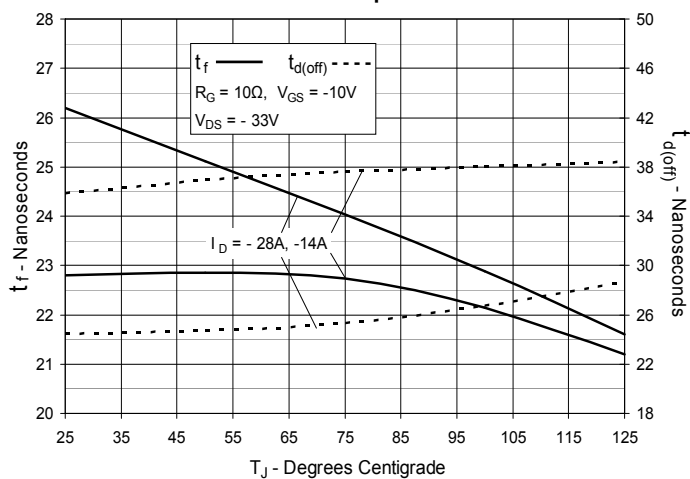
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



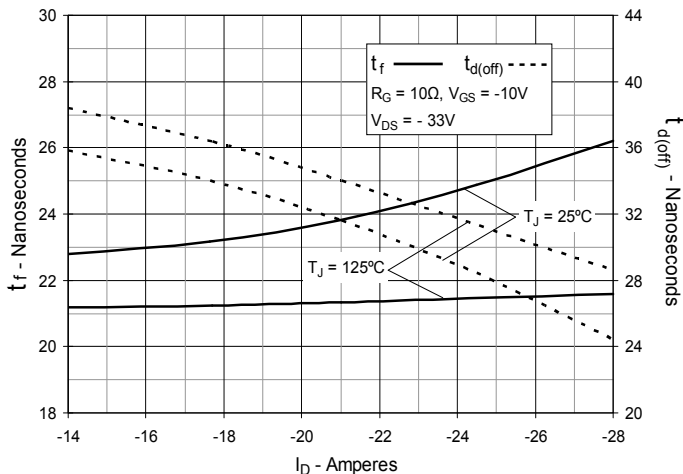
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

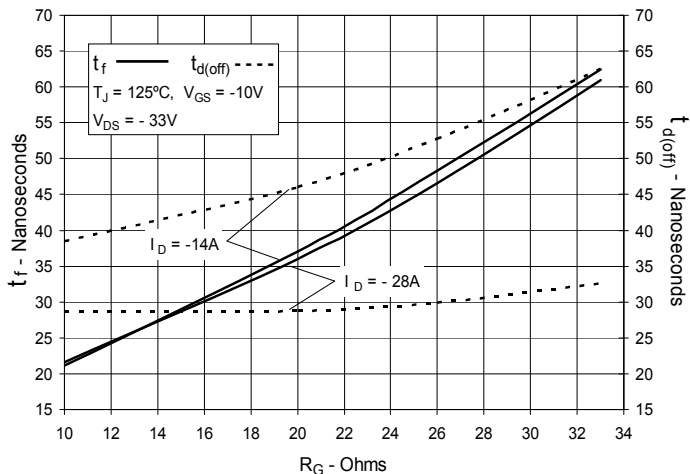


Fig. 19. Maximum Transient Thermal Impedance

